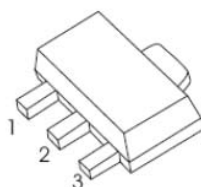


TRANSISTOR (PNP)

FEATURES

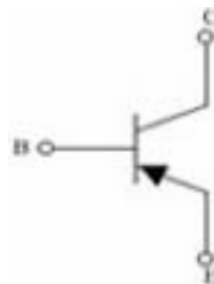
- Low speed switching
- High breakdown voltage
- Excellent current characteristics
- Low $V_{CE(sat)}$

SOT-89-3L



1. BASE
2. COLLECTOR
3. EMITTER

CIRCUIT DIAGRAM



MARKING : B772.

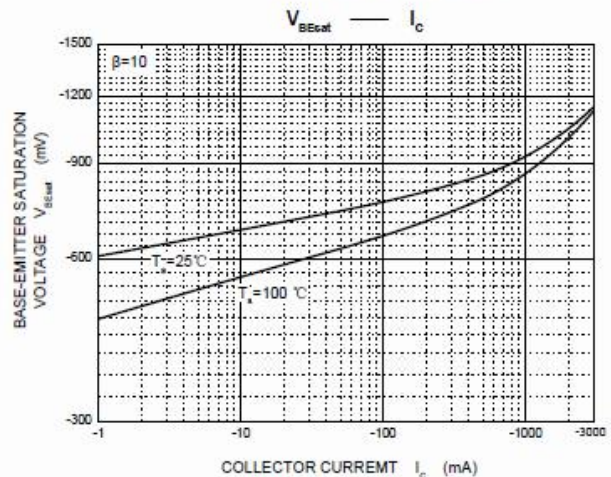
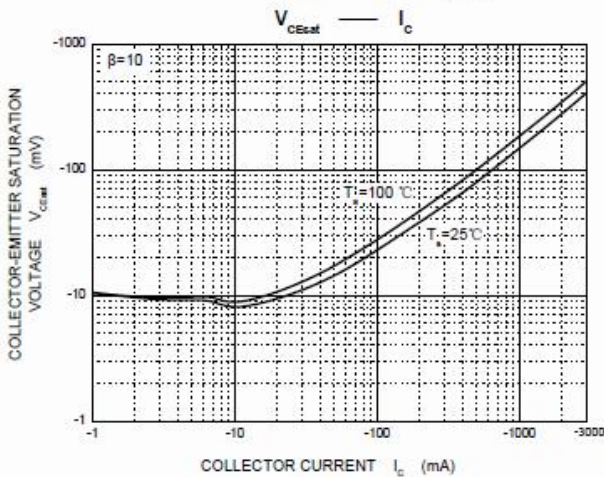
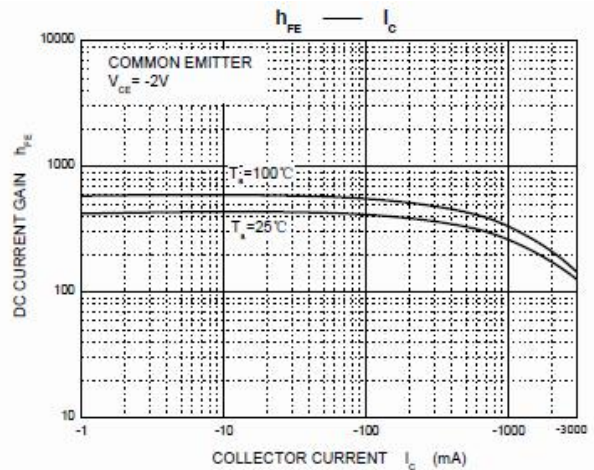
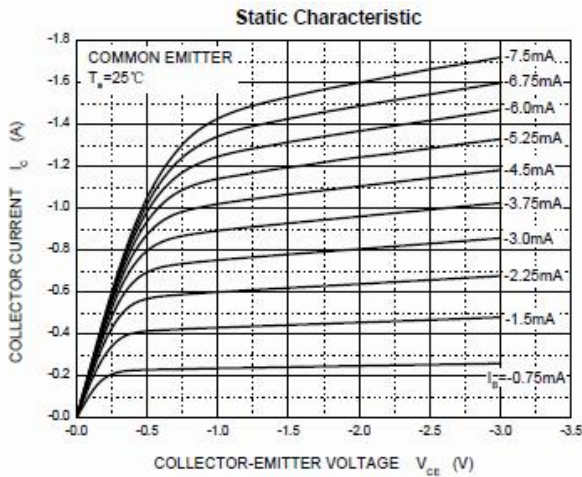
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_{CM}	-3	A
Power Dissipation	P_D	0.5	W
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55~150	$^{\circ}\text{C}$

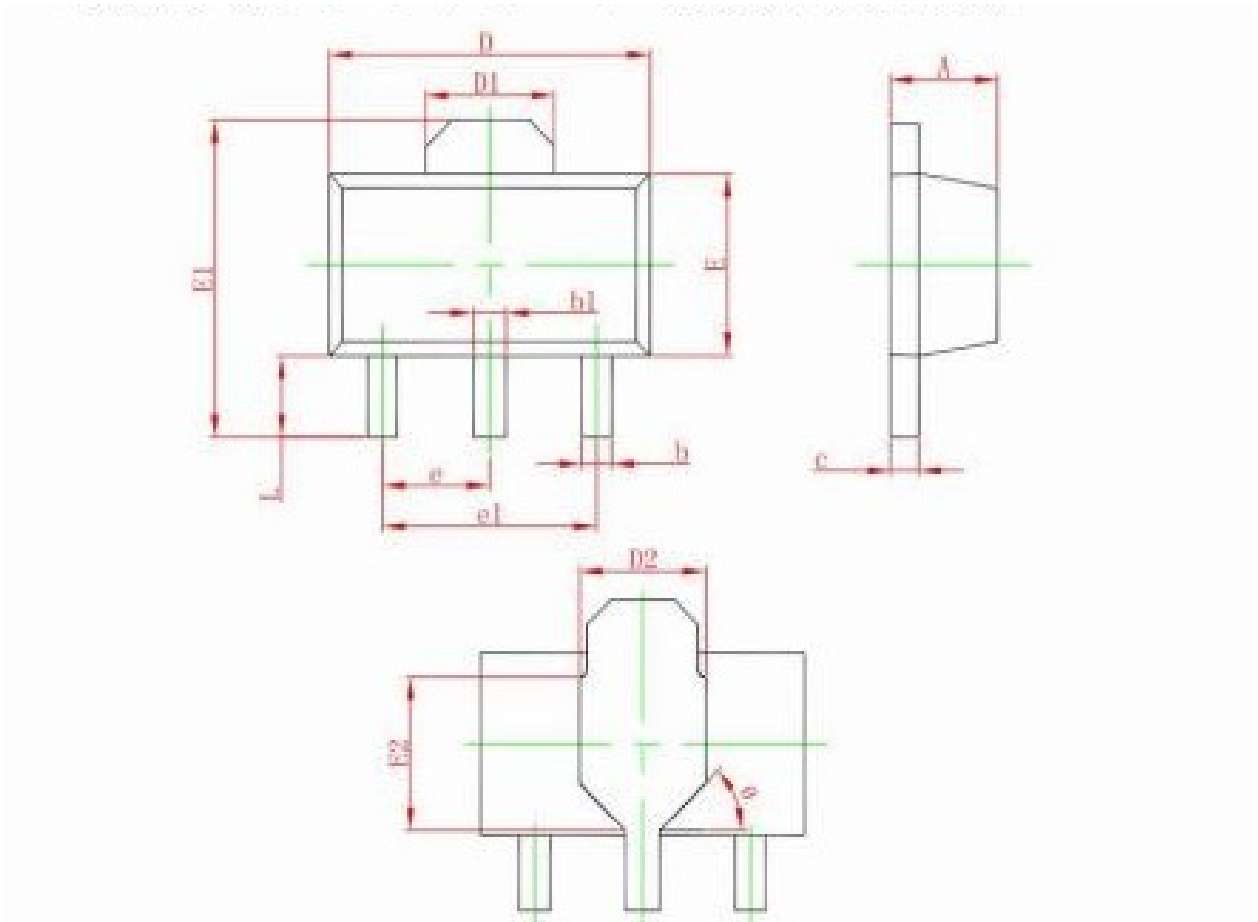
ELECTRICAL CHARACTERISTICS Ta=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Max	Unit
Emitter-base breakdown voltage	BV_{EBO}	$I_E=-100\mu A, I_C=0$	-6		V
Collector-base breakdown voltage	BV_{CBO}	$I_C=-100\mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C=-1mA, I_B=0$	-30		V
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$		-1	μA
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$		-1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-30V, I_B=0$		-10	μA
Collector-emitter saturation voltage	V_{CESAT}	$I_C=-2A, I_B=-0.2A$		-0.5	V
Base-emitter saturation voltage	V_{BESAT}	$I_C=-2A, I_B=-0.2A$		-1.5	V
DC current gain	h_{fe}	$V_{CE}=-2V, I_C=-1A$	160	320	
Transition frequency	f_T	$V_{CE}=-6V, I_C=-20mA$ $F=30MHZ$	150		MHZ

TYPICAL CHARACTERISTICS



SOT-89-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
D2	1.750 REF.		0.069 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
E2	1.900 REF.		0.075 REF.	
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047
θ	45°		45°	